



ZXMP2120E5

200V P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	Rds(on) max	I _{D MAX} T _A = +25°C
-200V	28Ω @ V _{GS} = -10V	-122mA

Description

This new generation trench MOSFET features a unique structure combining the benefits of low on-resistance and fast switching, making it ideal for high-efficiency power management applications.

Applications

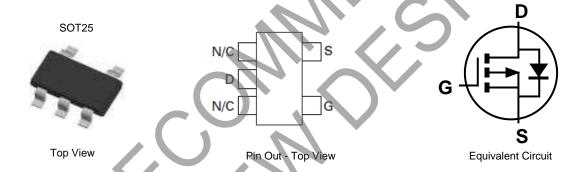
 Active Clamping of Primary Side MOSFETs in 48V DC-DC Converters

Features and Benefits

- High Voltage
- Low On-Resistance
- Fast Switching Speed
- Low Gate Drive
- Low Threshold
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: SOT25
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish @3
- Weight: 0.016 grams (Approximate)



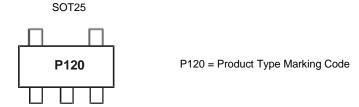
Ordering Information (Note 4)

Part Number	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
ZXMP2120E5TA	P120	7	8	3,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- See http://www.diodes.com/quality/lead_free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information





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June 2018

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Maximum Ratings (@ $T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V _{DSS}	-200	V
Gate-Source Voltage	V _{GSS}	±20	V
Continuous Drain Current (V _{GS} = -10V; T _A = +25°C) (Note 5)	I _D	-122	mA
Pulsed Drain Current (Note 6)	I _{DM}	-0.7	A
Pulsed Source Current (Body Diode) (Note 6)	I _{SM}	-0.7	A

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation at T _A = +25°C (Note 5) Linear Derating Factor	P _D	0.75 6	W mW/°C
Thermal Resistance, Junction to Ambient (Note 5)	R _{0JA}	167	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

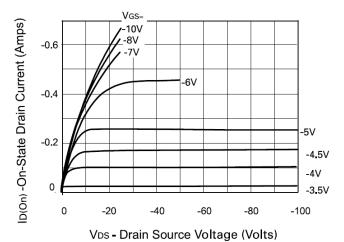
Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

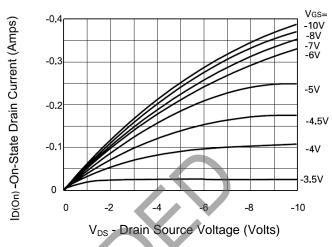
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage	BV _{DSS}	-200	-	-	٧	$V_{GS} = 0V$, $I_D = -1mA$	
Zero Gate Voltage Drain Current	IDSS	-).	-10 -100	μA	$V_{DS} = -200V, V_{GS} = 0V$ $V_{DS} = -160V, V_{GS} = 0V, T_A = +125^{\circ}0$	
Gate-Source Leakage	Igss	-	-	20	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS							
Gate Threshold Voltage	$V_{GS(TH)}$	-1.5	-	-3.5	V	$V_{DS} = V_{GS}$, $I_D = -1mA$	
Static Drain-Source On-Resistance (Note 7)	R _{DS(ON)}		-	28	Ω	$V_{GS} = -10V, I_D = -150mA$	
Forward Transconductance (Notes 7 & 8)	9 _{fs}	50	-	-	ms	$V_{DS} = -25V, I_{D} = -150mA$	
On-State Drain Current (Note 7)	I _D (ON)	-300	-	-	mA	V _{DS} = -25V, V _{GS} = -10V	
DYNAMIC CHARACTERISTICS							
Input Capacitance (Note 8)	Ciss	_	-	100	pF	V 05V V 0V	
Output Capacitance (Note 8)	Coss	-	-	25	pF	$V_{DS} = -25V, V_{GS} = 0V,$ f = 1.0MHz	
Reverse Transfer Capacitance (Note 8)	C _{rss}	-	-	7	pF	= 1.0WHZ	
Turn-On Delay Time (Notes 8 & 9)	t _{D(ON)}	-	-	7	ns		
Turn-On Rise Time (Notes 8 & 9)	t _R	-	-	15	ns	V 25V I 450mA	
Turn-Off Delay Time (Notes 8 & 9)	t _{D(OFF)}	-	-	12	ns	$V_{DD} = -25V, I_{D} = -150mA$	
Turn-Off Fall Time (Notes 8 & 9)	t _F	-	-	15	ns		
Notes: 5. For a device surface mounted on 25mm x 25mm FR-4 PCB with high coverage of single sided 1oz copper, in still air conditions. 6. Repetitive rating - pulse width limited by maximum junction temperature. Refer to Transient Thermal Impedance graph. 7. Measured under pulsed conditions. Pulse width ≤ 300μs. Duty cycle ≤ 2%. 8. Sample test. 9. Switching characteristics are independent of energing junction temperature.							

- Switching characteristics are independent of operating junction temperature.



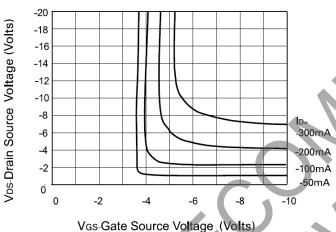
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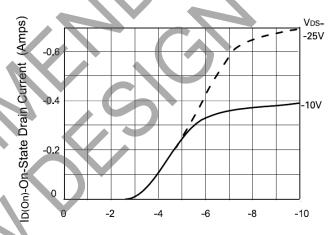




Output Characteristics

Saturation Characteristics

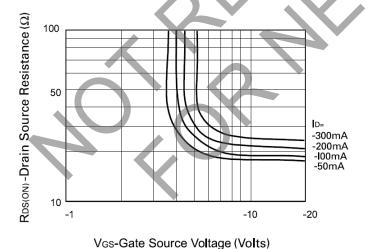


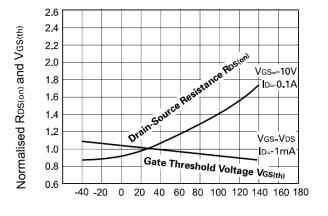


Vgs-Gate Source Voltage (Volts)

Voltage Saturation Characteristics





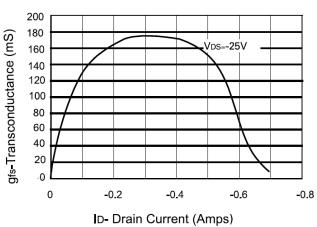


On-resistance vs gate-source voltage

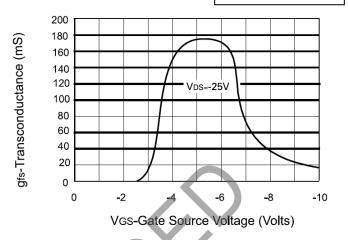
T-Temperature (°C) Normalised RDS(on) and VGS(th) vs Temperature



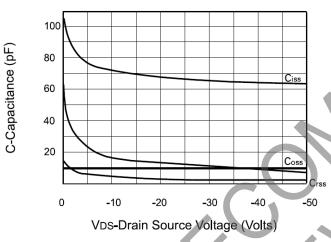
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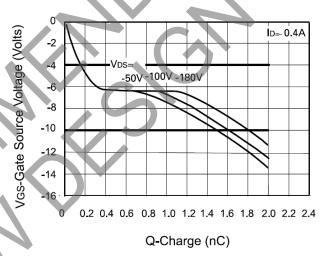
Transconductance v drain current



Transconductance v gate-source voltage



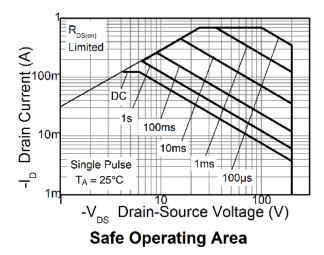
Capacitance v drain-source voltage

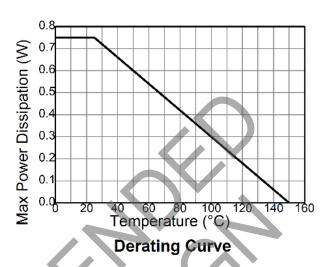


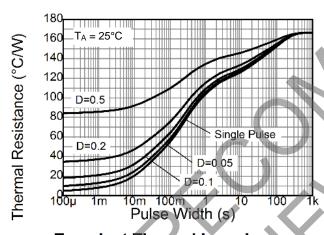
Gate charge v gate-source voltage

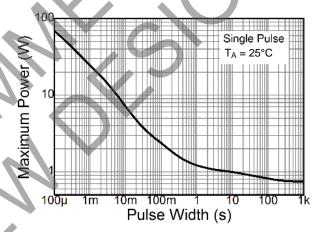


Thermal Characteristics









Transient Thermal Impedance

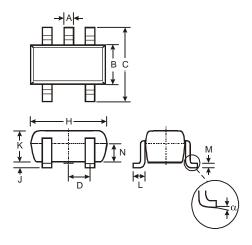
Pulse Power Dissipation

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Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT25

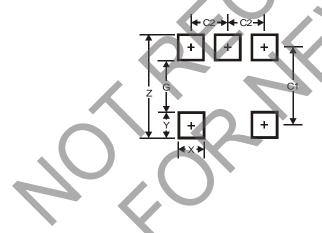


SOT25				
Dim	Min	Max	Тур	
Α	0.35	0.50	0.38	
В	1.50	1.70	1.60	
C	2.70	3.00	2.80	
ם	1	J	0.95	
Η	2.90	3.10	3.00	
7	0.013	0.10	0.05	
K	1.00	1.30	1.10	
1	0.35	0.55	0.40	
M	0.10	0.20	0.15	
2	0.70	0.80	0.75	
α	0°	8°	- 1	
All Dimensions in mm				

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT25



Dimensions	SOT25		
Z	3.20		
G	1.60		
Х	0.55		
Y	0.80		
C1	2.40		
C2	0.95		



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